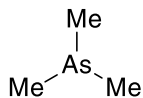


Catalog # 33-3750 Trimethylarsine, 99%



## Thermal Behavior:

- Melting point: -87.3°C
- Boiling point: 56°C

## Technical Notes:

1. CVD precursor for arsenic thin film deposition

Target Deposit	Deposition Technique	Delivery Temperature	Pressure	Co-reactants	Deposition Temperature	Ref.
GaAs	CVD	RT	60 Torr	GaMe <sub>3</sub> , H <sub>2</sub>	450-600°C	1
InGaAs	CVD	RT	200 Torr	InMe <sub>3</sub> , GaMe <sub>3</sub> , H <sub>2</sub>	580-630°C	2

## References:

1. [J. Cryst. Growth 1995, 147, 256](#)
2. [J. Cryst. Growth 1999, 197, 755](#)